

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.020AUSAPPLICATION NO.
09/997,396INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(SEE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hujanen et al.FILING DATE
November 28, 2001GROUP
2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	6,342,277 B1	1/29/02	Sherman			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

EXAMINER INITIAL	

RECEIVED
JAN 27 2003
TECHNOLOGY CENTER 2800

W:\DOCS\ASAVASA-13494.DOC
010303

EXAMINER

Shuland

DATE CONSIDERED

02/26/03

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORMPTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMMC.020AUS	APPLICATION NO. 09/997,396
	APPLICANT HUJANEN et al.	
	FILING DATE November 28, 2001	GROUP 2818

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1.	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
DV	2.	5,711,811	01/27/98	Suntola et al.	118	711	11/28/95

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
DV	3.	WO 00/38191	29.06.00	PCT				
DV	4.	WO 01/88972 A1	22.11.01	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)							
DV	5.	Addison, C. C. et al., "The Vapour Pressure of Anhydrous Copper Nitrate, and its Molecular Weight in the Vapour State," <u>J. Chem. Soc.</u> , pp. 3099-3106 (1958).						
	6.	Akerman, J. J. et al., "Identifying Tunneling in Ferromagnetic-Insulator-Ferromagnetic Thin Film Structures," World-wide web, physics.ucsd.edu/kuksgrp/Tunneling.html, pp. 1-6.						
	7.	Bobo, J. F. et al., "Spin-dependent tunneling junctions with hard magnetic layer pinning," <u>Journal of Applied Physics</u> , Vol. 83, No. 11, pp. 6685-6687 (1998).						
	8.	Daughton, J. M., World-wide web nve.com/otherbiz/mram2.pdf, "Advanced MRAM Concepts," pp. 1-6 (February 7, 2001).						
	9.	Fereday, R. J. et al., "Anhydrous Cobalt (III) Nitrate," <u>Chemical Communications</u> , p. 271 (1968).						
	10.	Imai, Takuji, World-wide web nikkeibp.asiabiztech.com/nea/200008/tech_108675.html, "100 Gbit/Inch HDD Just Around the Corner," pp. 1-6 (August 2000).						
	11.	Nielsen, O. et al., "Thin film deposition of lanthanum manganite perovskite by the ALE process," <u>Journal of materials Chemistry</u> , Vol. 9, pp. 1781-1784 (1999).						
	12.	Pakrad, C. D., "Pure Tech: Growth of MR/GMR Head Materials," World-wide web, puretechinc.com/tech_papers/tech_papers-4.htm, pp. 1-2 (1999).						
	13.	Suntola, <u>Handbook of Crystal Growth</u> , Vol. 3, Thin films and epitaxy, Part B: Growth mechanisms and dynamics, Chapter 14, pp. 601-663, Hurle, ed. Elsevier Science B.V. (1994).						
	14.	Wang, Shan X., "Advanced materials for Extremely High Density Magnetic Recording Heads," Department of Materials Science and Engineering, Department of Electrical Engineering, Stanford University, Stanford, CA 94305-4045, presentation.						
	15.	World-wide web megahaus.com/tech/westemdigital/shitepapers/gmr_wp.shtml, "GMR Head Technology: Increased Areal Density and Improved Performance Areal Density," pp. 1-4 (February 2000).						
	16.	World-wide web semiconductor.net/semiconductor/issues/Issues/1998/feb98/docs/emerging.asp, "GMR Read-Write Heads Yield Data Storage Record," pp. 1-2 (February 1998).						
	17.	World-wide web stoner.leeds.ac.uk/research/gmr.htm, "Giant Magnetoresistance," pp. 1-6.						
DV	18.	World-wide web, pc.guide.com/ref/hdd/op/heads/techGMR-c.html, "Giant Magnetoresistive (GMR) Heads," pp. 1-4.						

W:\DOCS\ANM\ANM-2847.DOC
021802

EXAMINER <i>Shuland</i>	DATE CONSIDERED <i>02/20/03</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.020AUSAPPLICATION NO.
09/997,396INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(SEE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hujanen et al.FILING DATE
November 28, 2001GROUP
2818W:\DOCS\ANM\ANM-4150.DOC
110802

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	6,006,763	12/28/99	Mori et al.			

W:\DOCS\ANM\ANM-4158.DOC
110802

EXAMINER

ghuland

DATE CONSIDERED

02/20/03

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.